

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	1219	"257"/\$.CCLS. and ((SOI) or (silicon adj2 insulator)) and (channel adj length) and source and drain and (channel near3 (dop\$4 or concentration\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 13:06
L3	482	"257"/\$.CCLS. and ((SOI) or (silicon adj2 insulator)) and (channel adj length) same (channel near3 (dop\$4 or concentration\$1 or impurit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 13:09
L4	426	"257"/\$.CCLS. and ((SOI)) and (channel adj length) same (channel near3 (dop\$4 or concentration\$1 or impurit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 13:13
L5	16	"257"/\$.CCLS. and ((SOI)) and (channel adj length with sub\$1micron) same (channel near3 (dop\$4 or concentration\$1 or impurit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 13:11
L6	161	"257"/\$.CCLS. and ((SOI)) and (channel adj length) same (channel near3 (concentration\$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:47
L7	2	((source or drain) adj concentration) with (threshold adj voltage)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:49
L8	0	((source or drain) adj concentration) with (drain adj current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:49
L9	0	((source or drain) adj concentration) same (drain adj current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:49
L10	23357	(drain adj current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:49

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L11	630	(drain adj current) with (drain with concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:49
L12	0	(drain adj current) with (drain adj concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:49
L13	83	(drain adj current) with (drain near3 concentration)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 14:50
S1	2052	"257"/\$.ccls. and (depletion adj mode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 15:02
S2	187	"257"/\$.ccls. and (depletion adj mode) and (SOI) and (MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:13
S3	263	(257/348).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 15:23
S4	57	"257"/\$.ccls. and ((depletion adj mode) with (MOSFET)) and (SOI)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:23
S5	280	"257"/\$.ccls. and ((depletion adj mode)) and (SOI)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 16:37
S6	1587	"257"/\$.ccls. and ((channel near2 dop\$3) and (SOI))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 20:23
S7	2	("6414353").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 17:33

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S8	499	(257/349).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 17:33
S9	2038	"257"/\$.ccls. and (depletion with (MOS or MOSFET))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 20:24
S10	392	"257"/\$.ccls. and ((depletion adj mode) with (MOS or MOSFET))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 20:51
S11	1082	"257"/\$.ccls. and (SOI with (advantag\$4))	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 20:52
S12	1075	"257"/\$.ccls. and (SOI with (advantag\$4))	USPAT	OR	OFF	2005/08/04 21:07
S13	2	("5952701").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 21:07
S14	586	257/347-349.CCLS. and (channel adj length)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/05 14:50
S15	2451	"257"/\$.CCLS. and ((SOI) or (silicon adj2 insulator)) and (channel adj length) and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/05 15:29
S16	1262	"438"/\$.CCLS. and ((SOI) or (silicon adj2 insulator)) and (channel adj length) and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/05 14:47
S17	126	"438"/149,479,517.CCLS. and ((SOI) or (silicon adj2 insulator)) and (channel adj length) and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/05 14:47
S18	346	257/347-349.CCLS. and (channel adj length) and (channel near3 (dop\$4 or concentration\$1 or impurit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/05 14:53

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S19	1312	"257"/\$.CCLS. and ((SOI) or (silicon adj2 insulator)) and (channel adj length) and source and drain and (channel near3 (dop\$4 or concentration\$1 or impurit\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/23 13:08
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